

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP1260F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

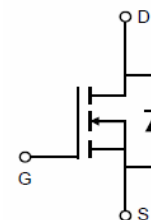
- $V_{DS} = 120V, I_D = 60A$
 $R_{DS(ON)} = 10m\Omega$ (typical) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

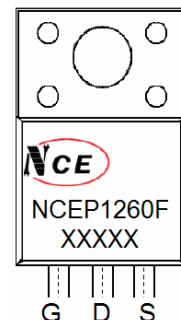
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

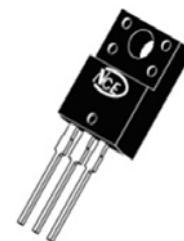
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-220F top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1260F	NCEP1260F	TO-220F	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	120	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Continuous($T_C = 100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	42.4	A
Pulsed Drain Current	I_{DM}	240	A
Maximum Power Dissipation	P_D	35	W
Derating factor		0.23	W/ $^\circ\text{C}$
Single pulse avalanche energy ^(Note 5)	E_{AS}	290	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	4.3	$^\circ\text{C/W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

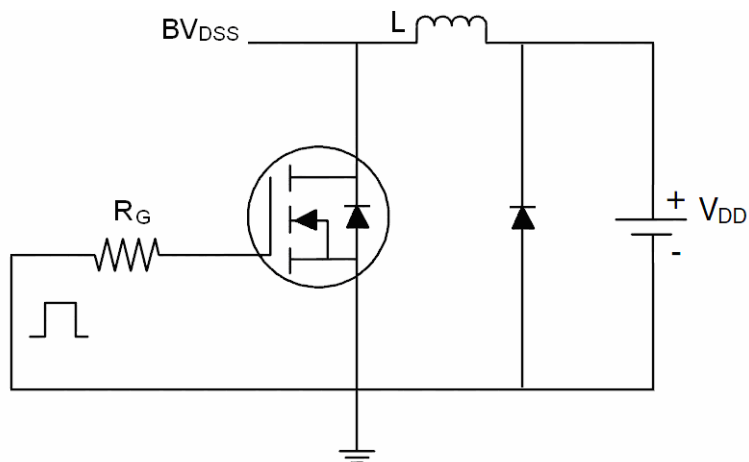
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	120		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =120V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	10	11	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =30A	-	40	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =60V, V _{GS} =0V, F=1.0MHz	-	2500	-	PF
Output Capacitance	C _{oss}		-	273	-	PF
Reverse Transfer Capacitance	C _{rss}		-	27	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =30A V _{GS} =10V, R _G =3Ω	-	11	-	nS
Turn-on Rise Time	t _r		-	7.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =60V, I _D =30A, V _{GS} =10V	-	37		nC
Gate-Source Charge	Q _{gs}		-	14		nC
Gate-Drain Charge	Q _{gd}		-	8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =60A	-		1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 100A/μs ^(Note3)	-	58		nS
Reverse Recovery Charge	Q _{rr}		-	149		nC

Notes:

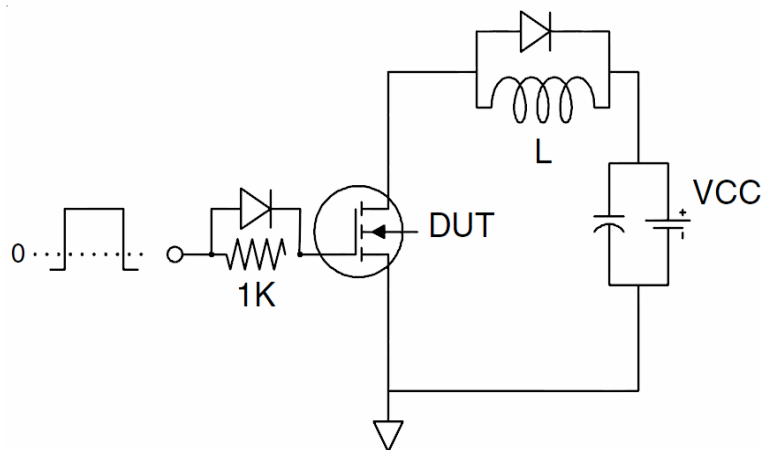
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

Test Circuit

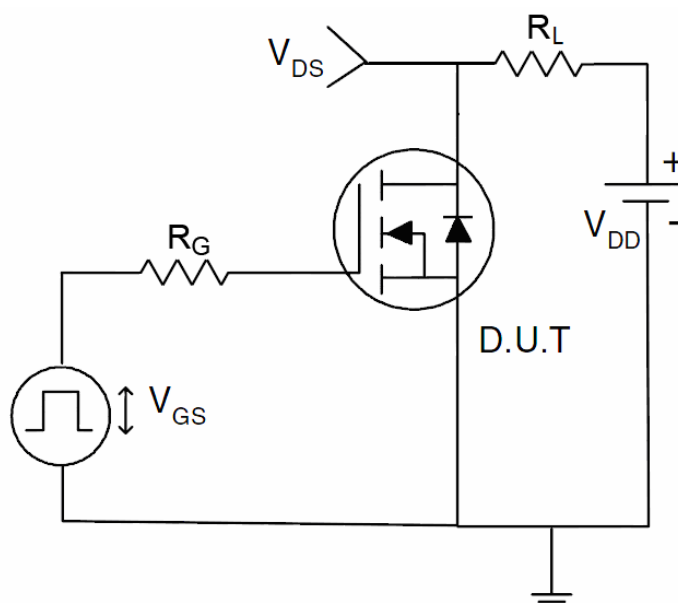
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

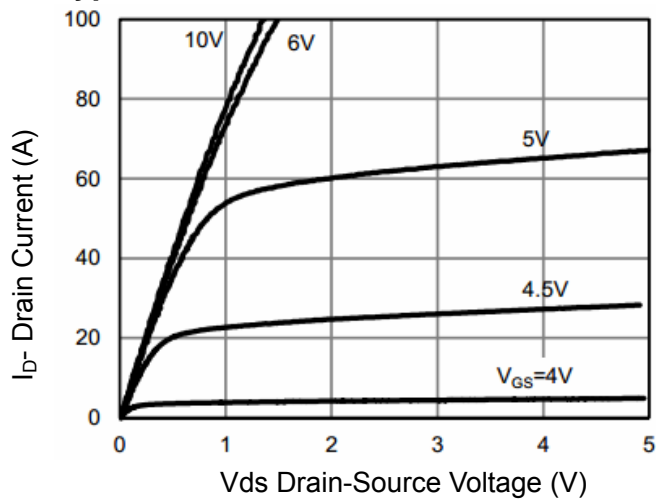


Figure 1 Output Characteristics

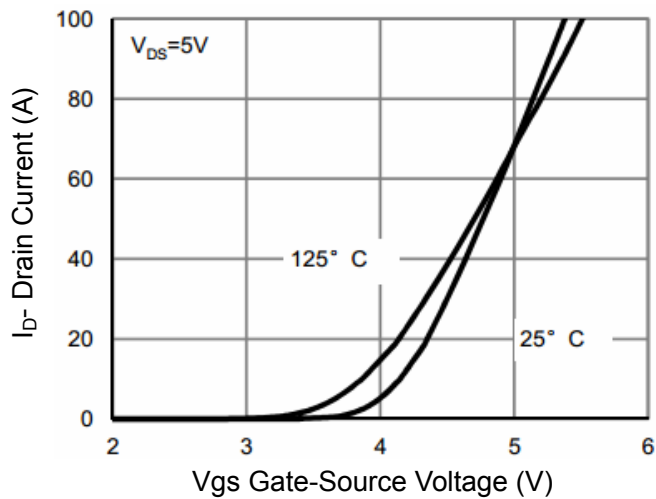


Figure 2 Transfer Characteristics

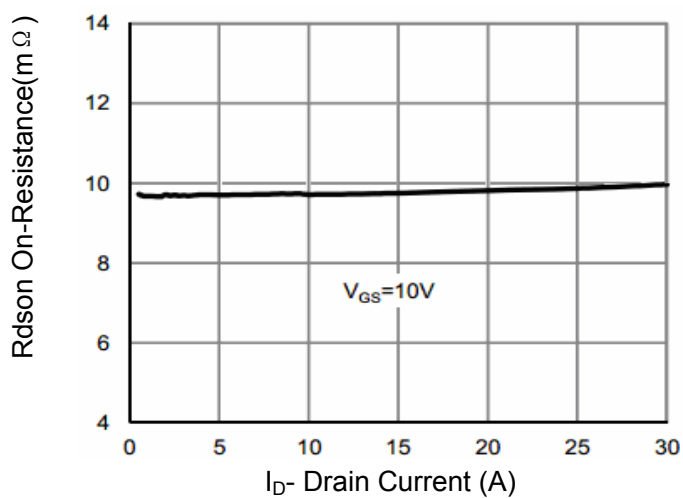


Figure 3 $R_{DS(on)}$ - Drain Current

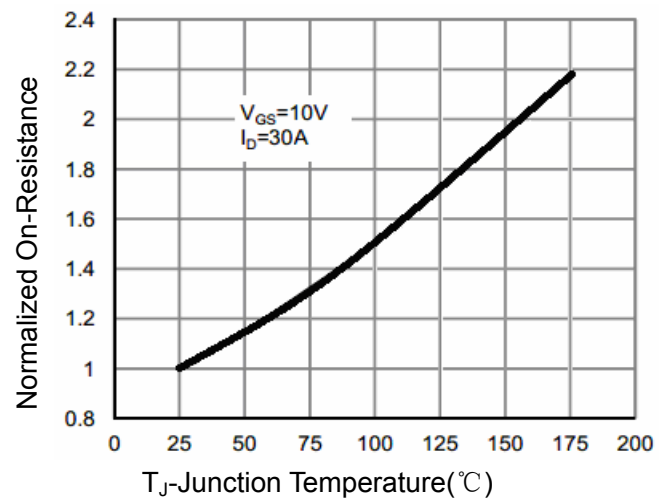


Figure 4 $R_{DS(on)}$ -Junction Temperature

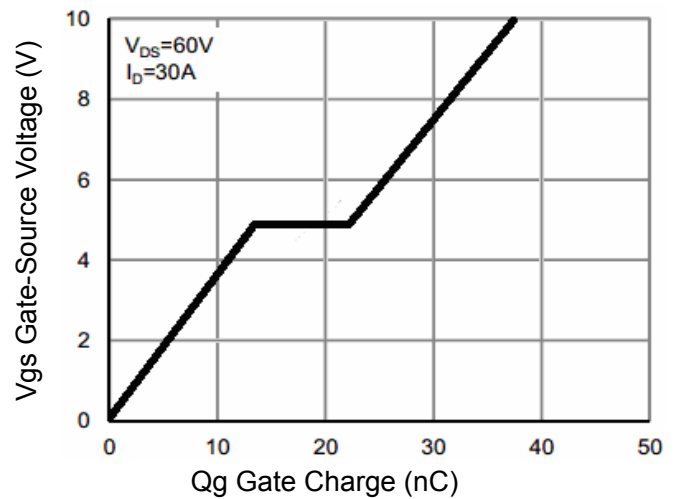


Figure 5 Gate Charge

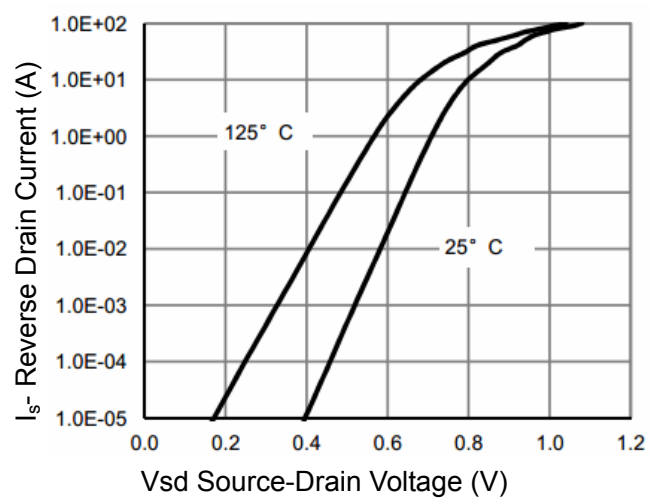


Figure 6 Source- Drain Diode Forward

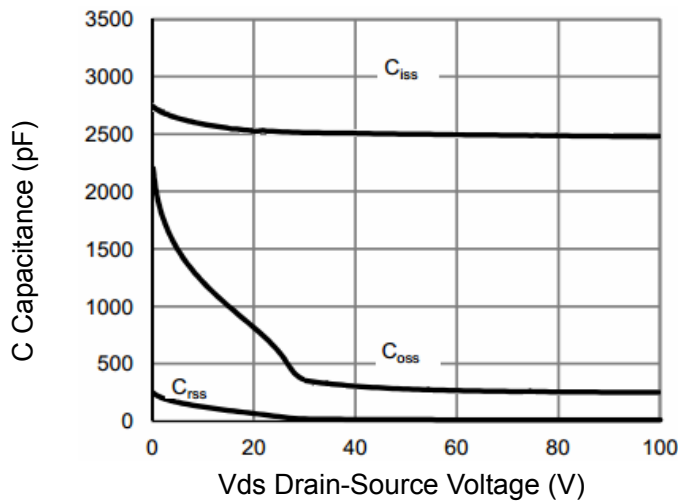


Figure 7 Capacitance vs Vds

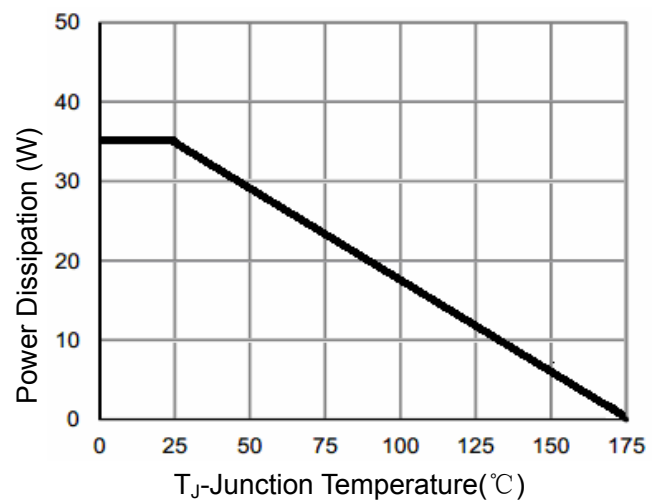


Figure 9 Power De-rating

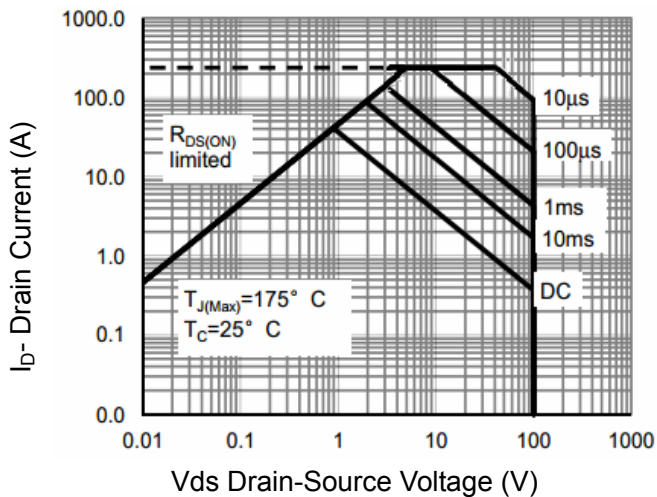


Figure 8 Safe Operation Area

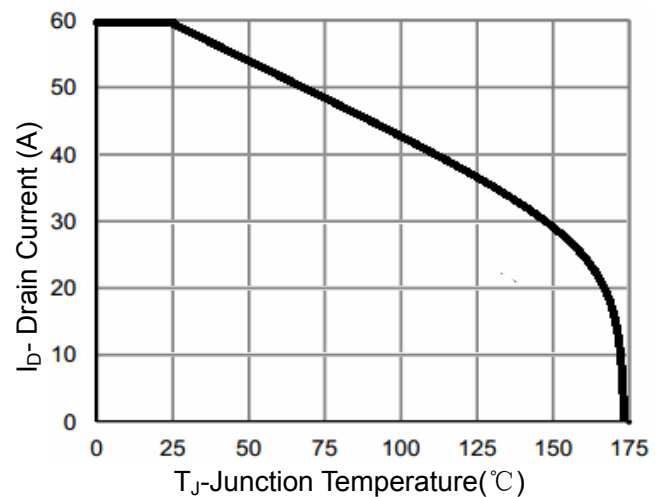


Figure 10 Current De-rating

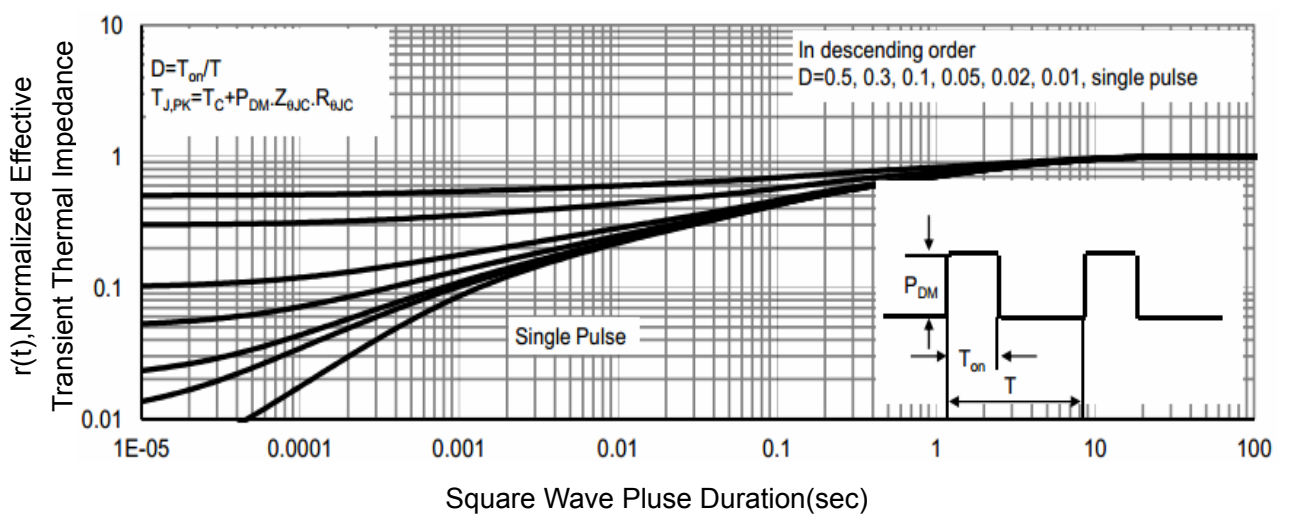
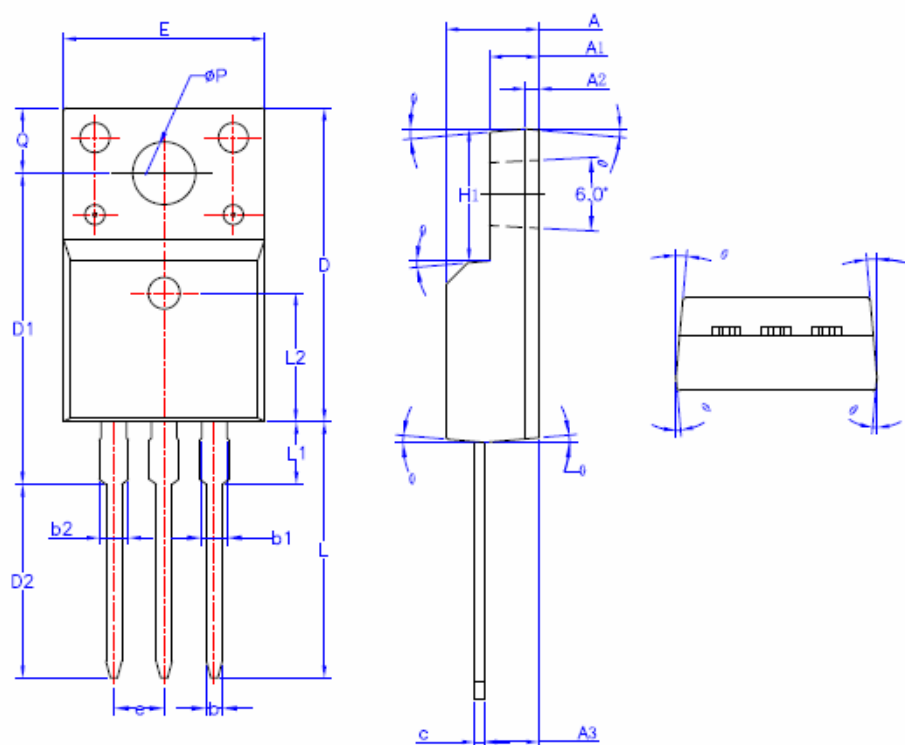


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220F Package Information



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.70	—	0.90
b1	1.18	—	1.38
b2	—	—	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e	2.54BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	—	—	3.50
L2	6.50REF		
øP	3.08	3.18	3.28
Q	3.20	—	3.40
θ 1	1°	3°	5°

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